

MMBT3904T SOT-523 Silicon General Purpose Transistor (NPN)

General description

SOT-523 Silicon General Purpose Transistor (NPN)

FEATURES

- · Simplifies Circuit Design
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- · Weight: approx. 0.002g

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

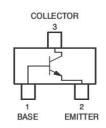
Symbol	Parameter	Value	Units
V сво	Collector-Base Voltage	60	V
VCEO	Collector-Emitter Voltage	40	V
V EBO	Emitter-Base Voltage	6	V
Ic	Collector Current	200	mA
P _D	Power Dissipation (FR-4 Board – minimum pad)	200	mW
Reja	Thermal Resistance from Junction to Ambient	600	°C /W
Тл Тэтс	Junction & Storage Temperature Range	-55 to +150	°C

Green Product



SOT-523 (SC-75A)

Electrical Symbol:



Device Marking:



. Off Characteristics

O mark to all		Total Consulting	Limits		Unit
Symbol	Parameter	Test Condition	Min	Max	
V (BR)CEO	Collector-Emitter Breakdown Voltage (Note 1)	I _C =1mA, I _B =0A	40	-	Volts
V _(BR) CBO	Collector-Base Breakdown Voltage	I _C =10uA, I _E =0A	60	-	Volts
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E =10uA, I _B =0A	6	-	Volts
lвь	Base Cutoff Current	V _{CE} =30V, V _{EB} =3V	-	50	nA
ICEX	Collector Cutoff Current	V _{CE} =30V, V _{EB} =3V	-	50	nA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%

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On Characteristics

Comple of	Downwater	Took Condition	Limits		Unit
Symbol	Parameter	Test Condition	Min	Max	
		I _C =0.1mA, V _{CE} =1V	40	-	
		I _C =1.0mA, V _{CE} =1V	70	-	
H _{FE}	DC Current Dain	I _C =10mA, V _{CE} =1V	100	300	-
		I _C =50mA, V _{CE} =1V	60	_	
		I _C =100mA, V _{CE} =1V	30	-	
	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA	-	0.2	
VCE(sat)		I _C =50mA, I _B =5mA	-	0.3	Volts
	Base-Emitter Saturation Voltage	I _C =10mA, I _B =1mA	0.65	0.85	
V BE(sat)		I _C =50mA, I _B =5mA	-	0.95	Volts

Small-signal Characteristics

Symbol	Parameter	Test Condition Limits		nits	– Unit	
	Farameter	rest condition	Min	Max	Oilit	
f⊤	Current-Gain-Bandwidth Product	I _C =10mA, V _{CE} =20V, f = 100MHz	200	-	MHz	
Cobo	Output Capacitance	V _{CB} =5V, I _E =0A, f = 1.0MHz	-	4	pF	
C _{ibo}	Input Capacitance	V _{BE} =0.5V, I _C =0A, f = 1.0MHz	-	8	pF	
h _{ie}	Input Impedancen	V _{CE} =10V, I _C =1mA, f = 1.0kHz	1	10	pF	
h _{re}	Voltage Feedback Ratio	V _{CE} =10V, I _C =1mA, f = 1.0kHz	0.5	8	X10 ⁻⁴	
h _{fe}	Small-signal Current Gain	V _{CE} =10V, I _C =1mA, f = 1.0kHz	100	400	-	
h _{oe}	Output Admittance	V _{CE} =10V, I _C =1mA, f = 1.0kHz 1		40	θ mhos	
NF	Noise Figure	V _{CE} =5V, I _C =100uA		5	dB	
INF	Noise Figure	Rs=1.0k Ω f = 1.0kHz		3	ub	

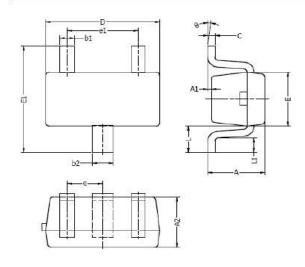
Switching Characteristics

Or made al	Danamatan	To at O an dition	Limits		11:4	
Symbol	Parameter	Test Condition	Min	Max	Unit	
t d	Delay Time	V _{CC} =3V, V _{BE} =0.5V,	_	35	nS	
t r	Rise Time	I _C =10mA, I _{B1} =1mA	-	35	113	
t s	Storage Time	Vcc = 3V, Ic = 10mA,	-	200	nS	
t f	Fall Time	I _{B1} = I _{B2} =1mA	-	50	110	

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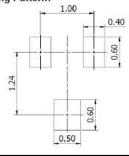


SOT-523 PACKAGE OUTLINE



DIM	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50	0.50 TYP.		TYP.
e1	0.90	1.10	0.035	0.043
L	0.40	.40 REF. 0.016 RE		REF.
L1	0.10	0.30	0.004	0.012
θ	0 °	8°	O°	8°

Typical Soldering Pattern:



- Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
 Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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